

#### **100V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23 PACKAGE**

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C (Note 6)
100\/	$700m\Omega @ V_{GS} = 10V$	0.76A
100V	900mΩ @ V <sub>GS</sub> = 6V	0.67A

#### Description

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### Applications

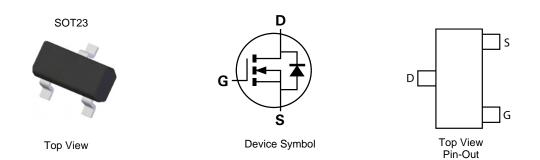
- DC-DC Converters
- Power Management Functions
- Motor Control
- Disconnect switches

#### **Features**

- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)



#### Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A07FTA	7N1	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

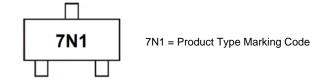
See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

ratiogen and Antimony neer Green products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500</li>
<1000ppm antimony compounds.</li>

4. For packaging details, go to our website at http://www.diodes.com

### **Marking Information**

Notes:







### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current	Steady State	@ $V_{GS} = 10V$ ; $T_A = +25^{\circ}C$ (Note 6) @ $V_{GS} = 10V$ ; $T_A = +70^{\circ}C$ (Note 6) @ $V_{GS} = 10V$ ; $T_A = +100^{\circ}C$ (Note 6) @ $V_{GS} = 10V$ ; $T_A = +25^{\circ}C$ (Note 5)	ID	0.8 0.6 0.5 0.7	A
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	3.5	A
Continuous Source Current (Body Diode) (Note 6)			ls	0.5	A
Pulsed Source Current (Body Diode) (Note 7)		I <sub>SM</sub>	3.5	A	

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

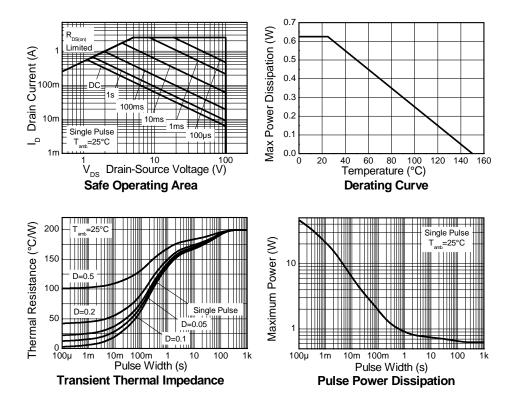
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	625	mW
Power Dissipation (Note 6)	PD	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

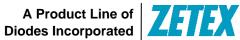
6. For a device surface mounted on FR4 PCB measured at t  $\leq$  10 sec. 7. Repetitive rating - 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs – pulse width limited by maximum junction temperature. 8. Thermal resistance from junction to solder-point (at the end of the drain lead).

### **Thermal Characteristics**

Notes:





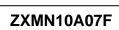


## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

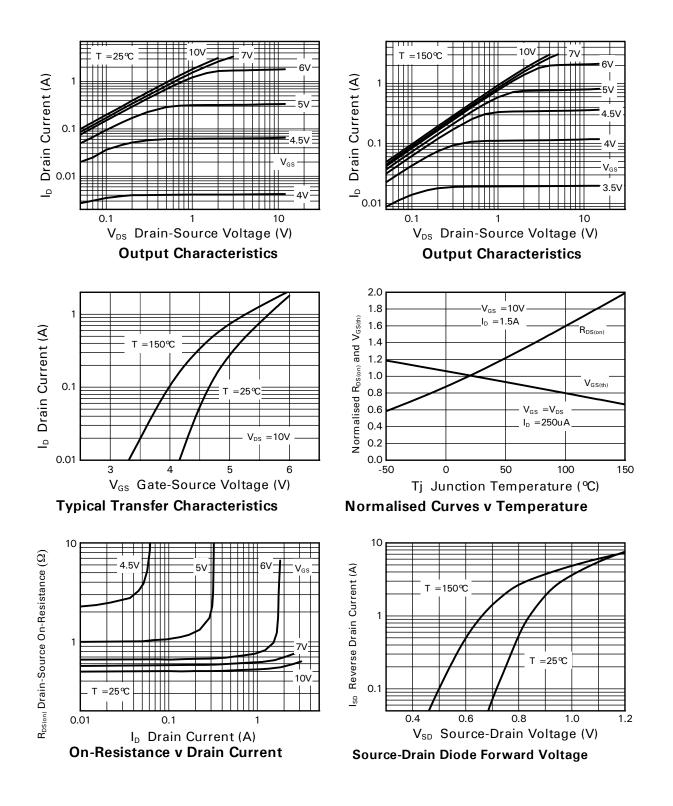
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS				1	r		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	—	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	2	—	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 9)	P		540	700	mΩ	$V_{GS} = 10V, I_D = 1.5A$	
	R <sub>DS (ON)</sub>	_	700	900	11152	$V_{GS} = 6V, I_D = 1A$	
Forward Transconductance (Notes 9 & 11)	<b>g</b> fs	—	1.6		S	$V_{DS} = 15V, I_D = 1A$	
Diodes Forward Voltage (Note 9)	V <sub>SD</sub>	—	0.85	0.95	V	$T_J = +25^{\circ}C, I_S = 1.5A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Notes 10 & 11)	C <sub>iss</sub>	—	138	280			
Output Capacitance (Notes 10 & 11)	C <sub>oss</sub>	—	12	25	pF	$V_{DS} = 50V$ , $V_{GS} = 0V$ , f = 1.0MHz	
Reverse Transfer Capacitance (Notes 10 & 11)	C <sub>rss</sub>	—	6	12		1 = 1.000112	
Gate Resistance (Notes 10 & 11)	R <sub>g</sub>	—	2	4	Ω	$f = 1MHz, V_{GS} = 0V, V_{DS} = 0V$	
Total Gate Charge (Notes 10 & 11)	Qg	_	2.9	6		$V_{GS} = 10V, V_{DS} = 50V,$	
Gate-Source Charge (Notes 10 & 11)	Q <sub>gs</sub>	_	0.7	1.5	nC		
Gate-Drain Charge (Notes 10 & 11)	Q <sub>gd</sub>	_	1	2		$I_D = 1A$	
Reverse Recovery Time (Note 11)	t <sub>rr</sub>	_	27	60	ns	T <sub>J</sub> = +25°C, I <sub>F</sub> = 1.8A,	
Reverse Recovery Charge (Note 11)	Q <sub>rr</sub>	_	12		nC	di/dt = 100A/µs	
Turn-On Delay Time (Notes 10 & 11)	t <sub>D(on)</sub>	_	1.8	_		$V_{GS} = 10V, V_{DD} = 50V,$	
Turn-On Rise Time (Notes 10 & 11)	tr	_	1.5	_			
Turn-Off Delay Time (Notes 10 & 11)	t <sub>D(off)</sub>	_	4.1	_	ns	$R_G = 6\Omega$ , $I_D = 1A$	
Turn-Off Fall Time (Notes 10 & 11)	t <sub>f</sub>	_	2.1		1		

9. Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%. 10. Switching characteristics are independent of operating junction temperature. 11. For design aid only, not subject to production testing. Notes:





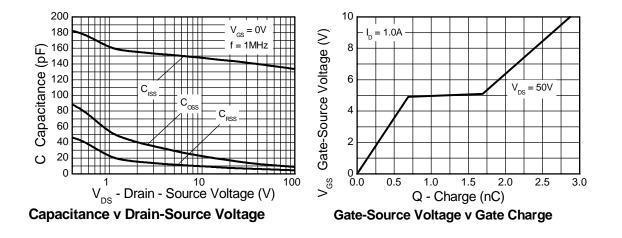
## **Typical Characteristics**



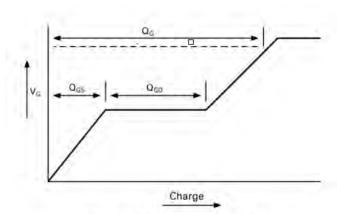




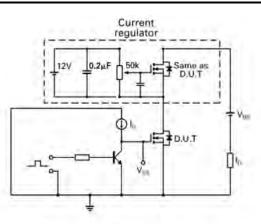
### Typical Characteristics (cont.)



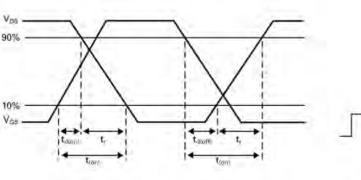
**Test Circuits** 



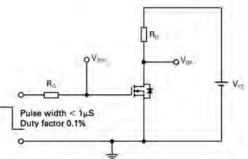




Gate charge test circuit



Switching time waveforms

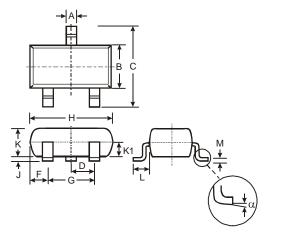


Switching time test circuit



## **Package Outline Dimensions**

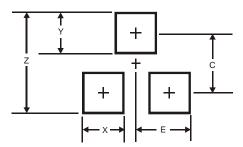
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
κ	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
Μ	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.9			
Х	0.8			
Y	0.9			
С	2.0			
E	1.35			



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